1. General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV3160Z-Q

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- · High collector current capability
- High collector current gain h_{FE} at high I_C
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · Electronic ballast for fluorecent lighting
- · LED driver for LED chain module
- LCD backlighting
- HID front lighting
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	600	V
I _C	collector current		-	-	0.1	Α

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C; C
2	С	collector		D .
3	Е	emitter		B — [
4	С	collector	1 2 3	Ė
			SC-73 (SOT223)	sym016



600 V, 0.1 A NPN high-voltage low VCEsat transistor

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PBHV2160Z-Q	SC-73	plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	<u>SOT223</u>

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV2160Z-Q	HV216Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	600	V
V_{CEO}	collector-emitter voltage	open base		-	600	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	600	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
Ic	collector current			-	0.1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1.4	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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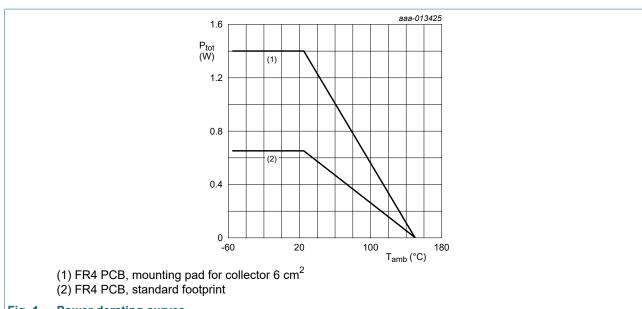


Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	190	K/W
	junction to ambient		[2]	-	-	89	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

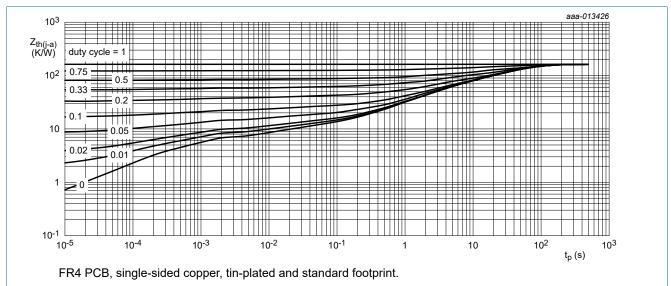
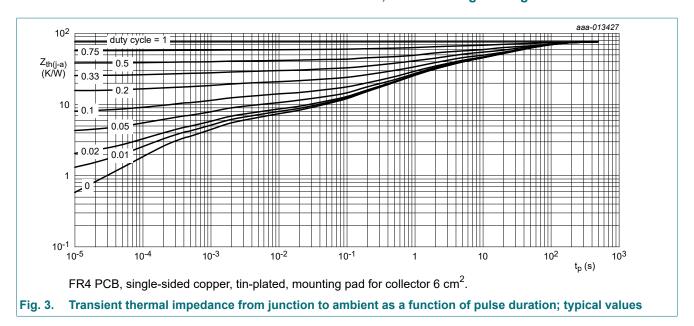


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	М	in	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 400 V; I _E = 0 A; T _{amb} = 25 °C	-		-	100	nA
	current	V _{CB} = 400 V; I _E = 0 A; T _j = 150 °C	-		-	10	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 4.8 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-		-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 400 V; V _{BE} = 0 V; T _{amb} = 25 °C	-		-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 10 mA; T _{amb} = 25 °C	70)	125	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 30 \text{ mA}; I_B = 6 \text{ mA}; T_{amb} = 25 \text{ °C}$	-		65	125	mV
V _{BEsat}	base-emitter saturation voltage	I_C = 50 mA; I_B = 5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-		-	950	mV
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$	-		1.7	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-		81	-	pF

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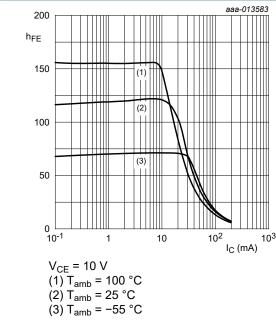


Fig. 4. DC current gain as a function of collector current; typical values

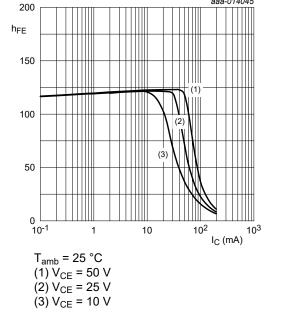
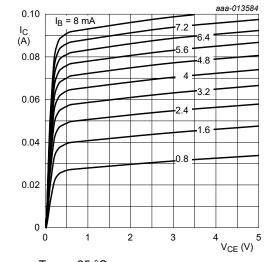
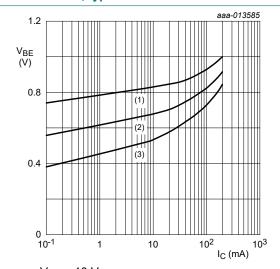


Fig. 5. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



 V_{CE} = 10 V

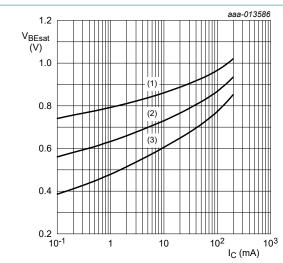
(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter voltage as a function of collector current; typical values

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$$I_{\rm C}/I_{\rm B} = 5$$

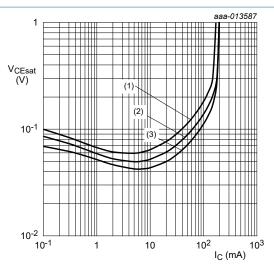
(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2) $T_{amb} = 25 \,^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) T_{amb}= 100 °C

Fig. 8. Base-emitter saturation voltage as a function of Fig. 9. collector current; typical values



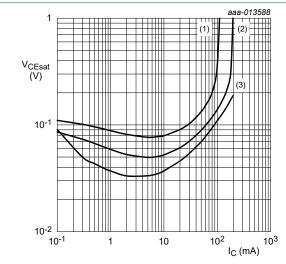
$$I_{\rm C}/I_{\rm B} = 5$$

$$(1) T_{amb} = 100 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

I_C/I_B = 5 (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -55 °C

Collector-emitter saturation voltage as a function of collector current; typical values



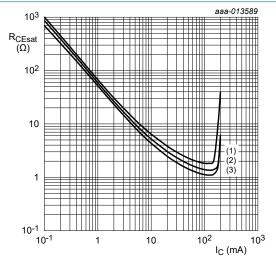
(1)
$$I_C/I_B = 10$$

(2) $I_C/I_B = 5$

(2)
$$I_C/I_B = 5$$

 $(3) I_{\rm C}/I_{\rm B} = 2.5$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

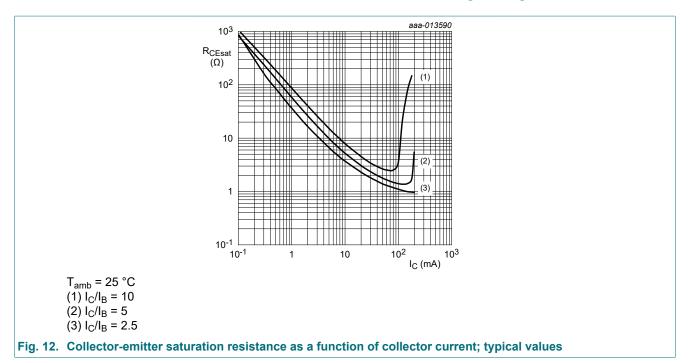
$$(1) T_{amb} = 100 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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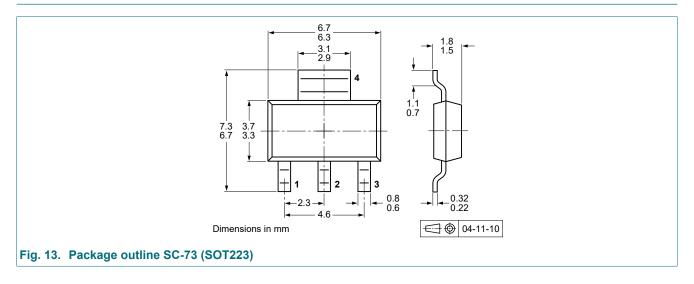


11. Test information

Quality information

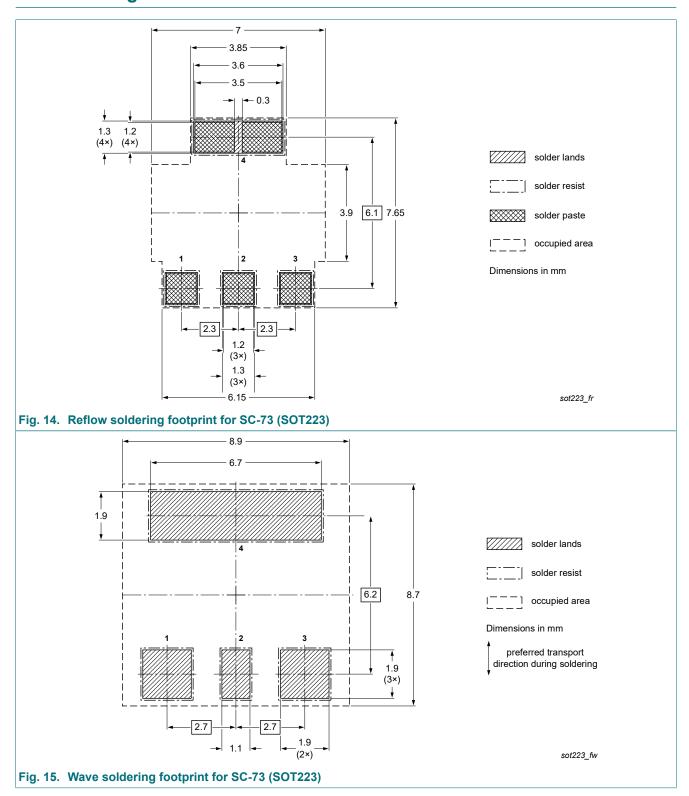
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



600 V, 0.1 A NPN high-voltage low VCEsat transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV2160Z-Q v.1	20230717	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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PBHV2160Z-Q

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